

GaAlAs T-1 PACKAGE

INFRARED EMITTING DIODE

MIE-324H4

Description

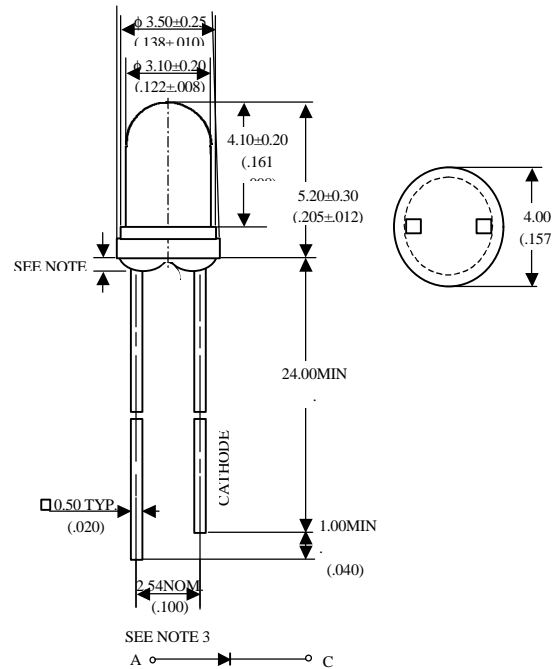
The MIE-324H4 is a GaAlAs infrared LED having a peak wavelength at 850nm. It features ultra-high power, high response speed and molded package with higher radiant intensity. In addition to improving the S/N ratio in applied optical systems, the MIE-324H4 has greatly improved long-distance characteristics as well as significantly increased its range of applicability .

Features

- Ultra-High radiant intensity
- High response speed
- Standard T-1 (ϕ 3mm) package, radiant angle : 40°
- Peak wavelength $\lambda_p = 850$ nm

Package Dimensions

Unit : mm (inches)



Notes :

1. Tolerance is ± 0.25 mm (.010") unless otherwise noted.
2. Protruded resin under flange is 1.5 mm (.059") max.
3. Lead spacing is measured where the leads emerge from the package.

Absolute Maximum Ratings

@ $T_A = 25^\circ\text{C}$

Parameter	Maximum Rating	Unit
Power Dissipation	120	mW
Peak Forward Current(300pps,10 μ s pulse)	1	A
Continuos Forward Current	100	mA
Reverse Voltage	5	V
Operating Temperature Range	-55°C to +100°C	
Storage Temperature Range	-55°C to +100°C	
Lead Soldering Temperature	260°C for 5 seconds	

Unity Opto Technology Co., Ltd.

02/04/2002

Optical-Electrical Characteristics

@ T_A=25°C

Parameter	Test Conditions	Symbol	Min.	Typ .	Max.	Unit
Radiant Intensity	I _F =20mA	I _e	-	2.1	-	mW/sr
Forward Voltage	I _F =50mA	V _F	-	1.5	1.8	V
Reverse Current	V _R =5V	I _R	-	-	100	μA
Peak Wavelength	I _F =20mA	λ _p	-	850	-	nm
Spectral Bandwidth	I _F =20mA	Δλ	-	30	-	nm
View Angle	I _F =20mA	2θ _{1/2}	-	40	-	deg .

Typical Optical-Electrical Characteristic Curves

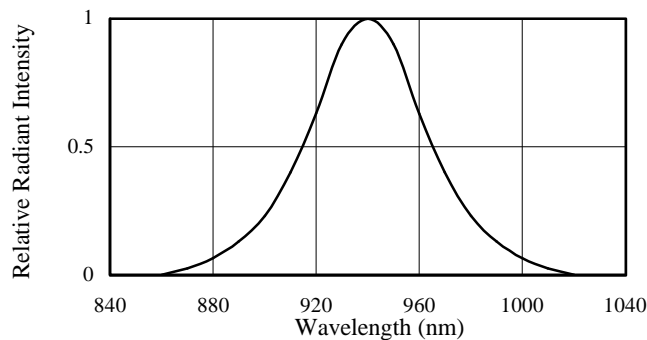


FIG.1 SPECTRAL DISTRIBUTION

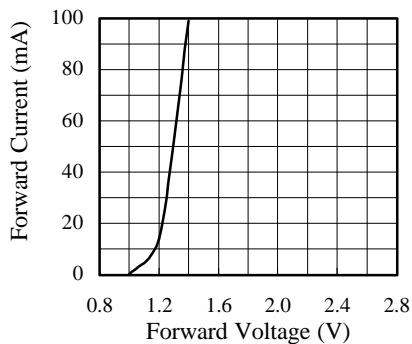


FIG.2 FORWARD CURRENT VS. FORWARD VOLTAGE

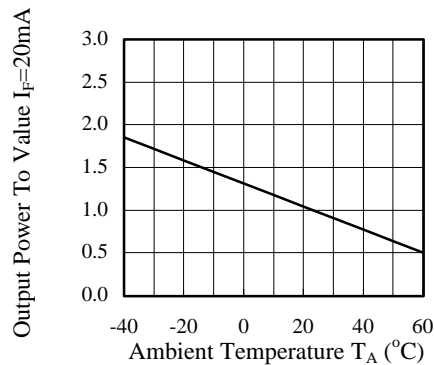


FIG.3 RELATIVE RADIANT INTENSITY VS.AMBIENT TEMPERATURE

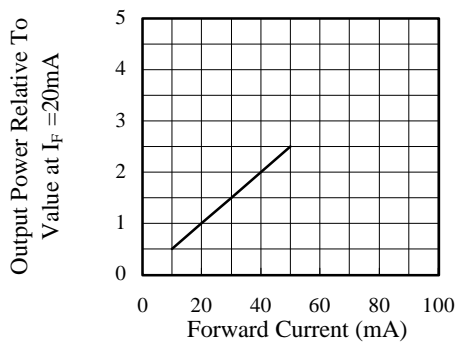


FIG.4 RELATIVE RADIANT INTENSITY VS. FORWARD CURRENT

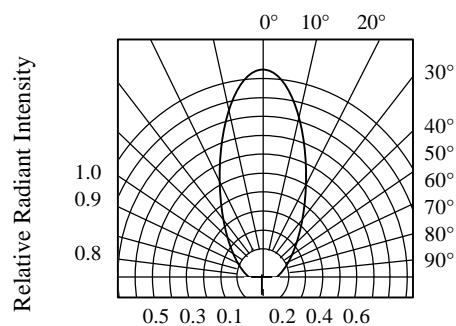


FIG.5 RADIATION DIAGRAM